

650V, 50A Silicon Carbide Schottky Diode

Features

- 650V Silicon Carbide Schottky Rectifier
- Zero Recovery Current
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- RoHS Compliant
- JEDEC Qualification



Cathode Anode



Applications

- General Rectification

Device	Package	Marking	Remark
TDCP50B65	TO-220-2L	TDCP50B65	RoHS

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	650	V
Reverse Blocking Voltage	V_R	650	V
Average Rectified Forward Current	$I_{F(AV)}$	50	A
Non-Repetitive Peak Surge Current 60Hz Single Half Sine Wave	I_{FSM}	500	A
Power Dissipation	$T_C = 25^\circ C$	250	W
	$T_C = 110^\circ C$	108	W
Operating Junction Temperature	T_J	-55 ~ 175	°C
Storage Temperature Range	T_{STG}	-55 ~ 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Typical Thermal Resistance, Junction-to-Case	R_{\thetaJC}	0.6	°C/W

Electrical Characteristics

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage Drop	V_F	$I_F=50A, T_C=25^\circ C$	--	1.62	2.12	V
		$I_F=50A, T_C=175^\circ C$	--	2.16	2.66	V
Reverse Leakage Current	I_R	$V_R = 650V, T_C=25^\circ C$	--	--	500	µA
Total Capacitive Charge ^(Note1)	Q_C	$V_R = 400V, I_F = 50A, dI/dt=400A/\mu s, T_C=25^\circ C$	--	208	--	nC
Total Capacitance	C	$V_R = 0V, T_C=25^\circ C, f=1MHz$	--	2210	--	pF

Notes :

(1) This is a majority carrier diode, so there is no reverse recovery charge.

Fig.1 Forward voltage drop vs. Forward current

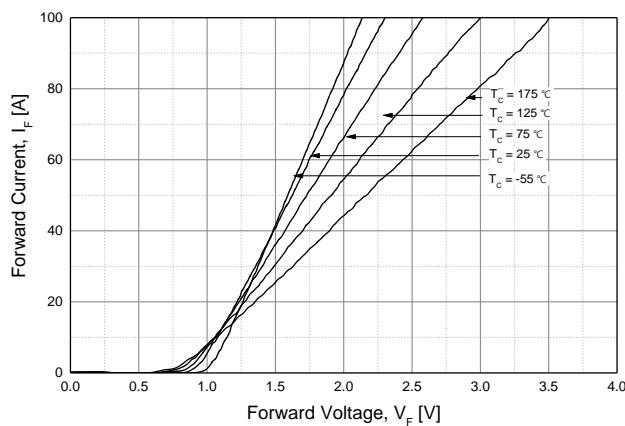


Fig 2. Reverse voltage vs. Reverse current

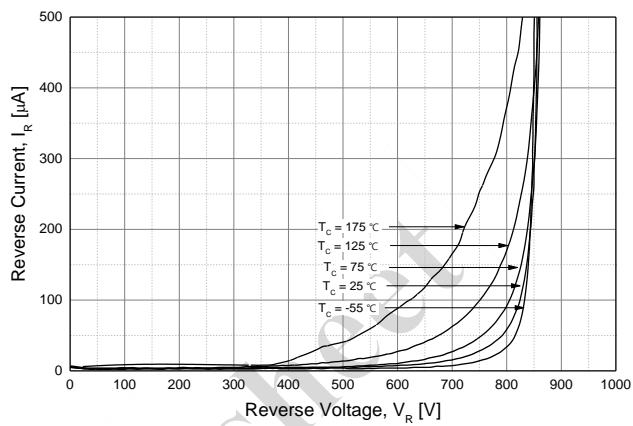


Fig 3. Reverse voltage vs. Reverse charge

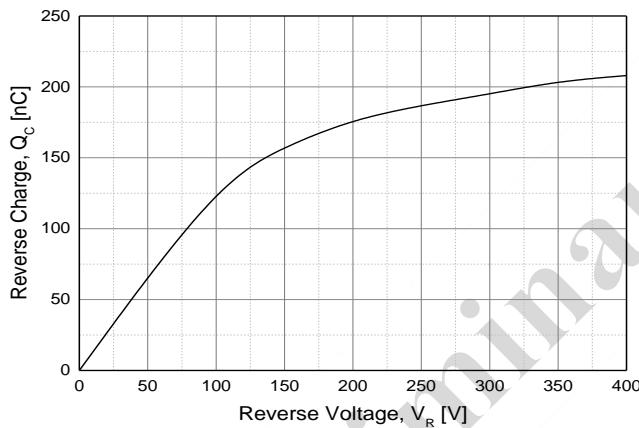


Fig 4. Capacitance

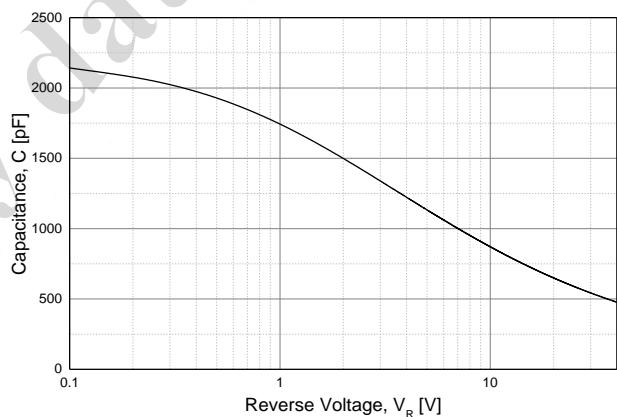


Fig 5. Case temperature vs. Power Dissipation

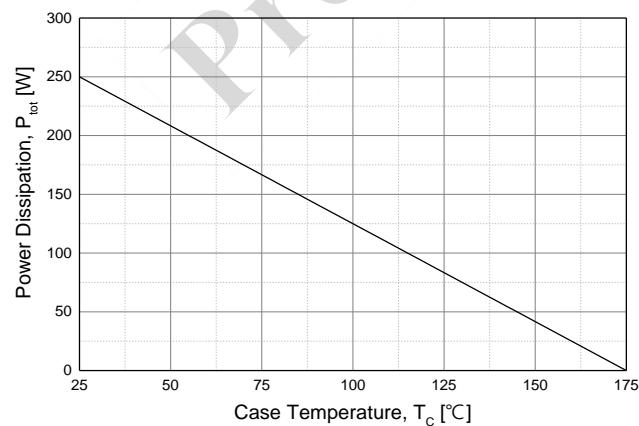
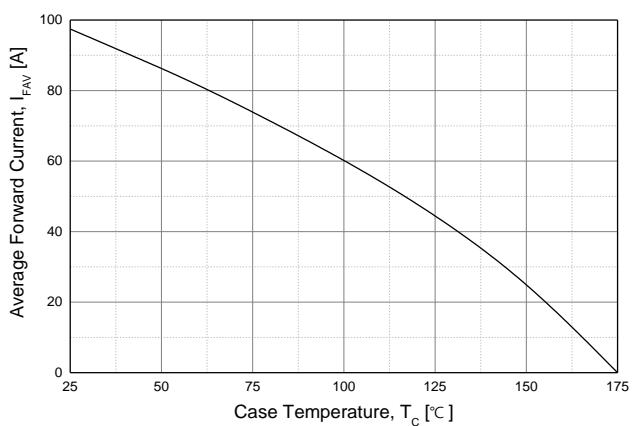
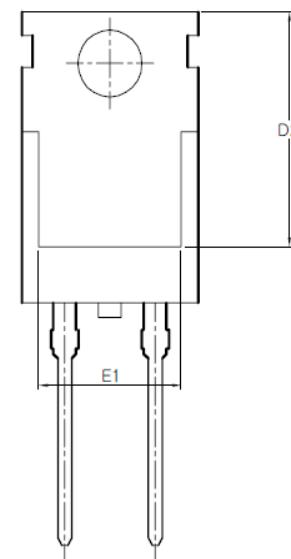
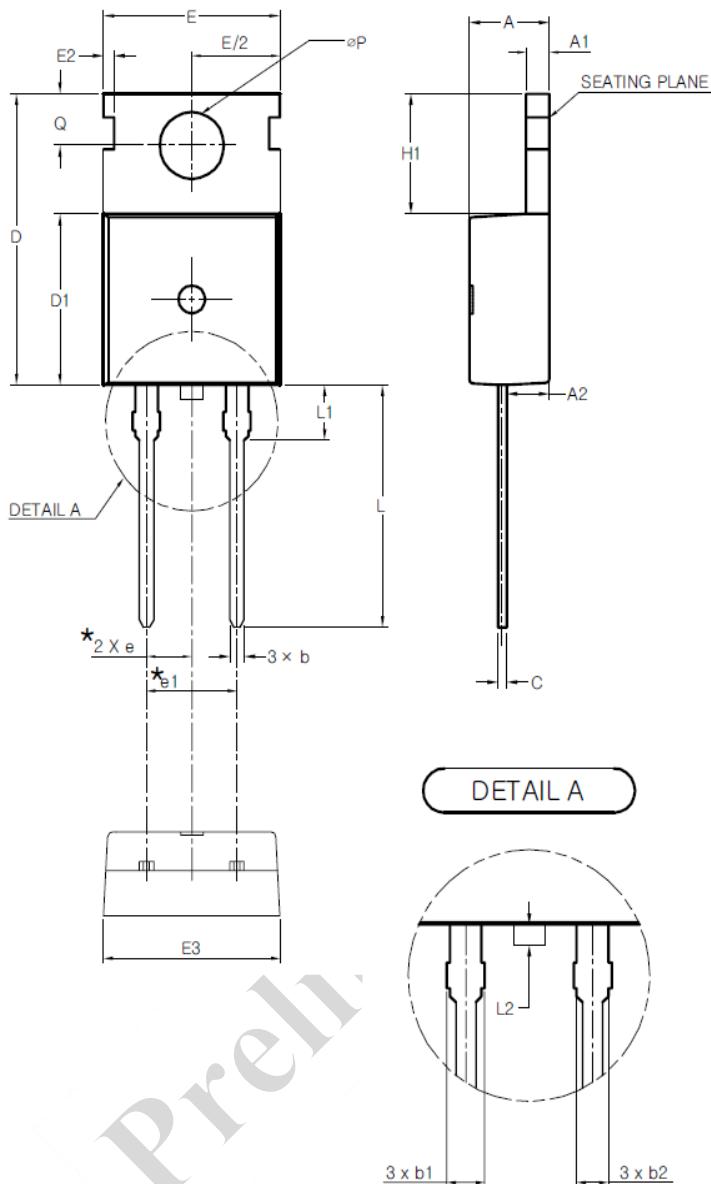


Fig 6. Case temperature vs. Forward current



TO-220-2L MECHANICAL DATA



SYMBOL	MIN	NOM	MAX
A	4.30	4.50	4.70
A1	1.25	1.30	1.40
A2	2.20	2.40	2.60
b	0.70	0.80	0.90
b1	1.42	1.52	1.62
b2	1.17	1.27	1.37
c	0.45	0.50	0.60
D	15.50	15.70	15.90
D1	9.00	9.20	9.00
D2	(12.70)		
*E	9.70	9.90	10.10
E1	(8.00)		
E2	(0.60)		
E3	9.70	9.90	10.10
e	2.54 BSC		
e1	5.08 BSC		
H1	6.30	6.50	6.70
L	12.88	13.08	13.28
L1	(3.00)		
L2	—	—	0.80
ØP	3.50	3.60	3.70
Q	2.70	2.80	2.90

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